Diode Semiconductor Device - Page 1 of 1



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Inc	losure Material:
Me	tal
Ov	erall Length:
Be	tween 0.200 inches and 0.250 inches
1.00 Ove 0.62 Fun Tran End 2gvo Mou	rminal Length:
	100 inches
	erall Diameter:
	25 inches
	nction For Which Designed:
	ansient suppressor
	d Application:
	vortac, fa-9996
	ounting Method:
	rminal
	rminal Circle Diameter:
0.0	151 inches
Se	miconductor Material:
Sili	icon
Vo	Itage Rating In Volts Per Characteristic:
31.	4 breakdown voltage, dc and 34.7 breakdown voltage, dc
Cu	rrent Rating Per Characteristic:
40.	00 milliamperes on-state current, dc
Sp	ecial Features:
Fu	nction, absorber, ovv; reference data, 1a2a2vr (typical), ti-6820.2, fa-9996, vortac, vor/dm
Те	rminal Type And Quantity:
2 u	ininsulated wire lead
Sh	elf Life:
N/a	a
Un	it Of Measure:
De	militarization:
No	
Fiig	g:
A1	10a0